Author Index of Volume 231

Angelo, J. E., 1

Ballingall, J. M., 95

Chand, N., 143
Chao, P. C., 95
Cohen, P. I., 1

Dabiran, A. M., 1
Duh, K. H. G., 95

Gerberich, W. W., 1
Gunshor, R. L., 190

Ho, P., 95

Kaneko, Y., 173
Kikuchi, A., 173
Kishino, K., 173
Kuo, J. M., 158

Lin, M. E., 197
Look, D. C., 61

Madhukar, A., 8
Martin, P. A., 95
Masselink, W. T., 86
Mazurowski, J., 95
Melloch, M. R., 74
Morkoç, H., 107, 125, 197
Mui, D. S. L., 107

Nomura, I., 173
Nurmikko, A. V., 190

Otsuka, N., 190

Ploog, K. H., 43

Smith, P. M., 95
Strite, S., 197

Tournié, E., 43

Wang, Z., 107

Zhou, G. L., 125

Subject Index of Volume 231

Aluminium nitride
progress and prospects for GaN and the III–V nitride semiconductors, 197

Diffusion
growth of high quality AlGaAs/GaAs heterostructures by molecular beam epitaxy for photonic and electronic device applications, 143

Electronic devices
growth of high quality AlGaAs/GaAs heterostructures by molecular beam epitaxy for photonic and electronic device applications, 143
transport of quasi-two-dimensional electrons in heterojunction field effect transistors, 86

Epitaxy
gas source molecular beam epitaxial growth and device applications in $In_{0.5}Ga_{0.5}P$ and $In_{0.5}Al_{0.5}P$ heterostructures, 158
growth of high quality AlGaAs/GaAs heterostructures by molecular beam epitaxy for photonic and electronic device applications, 143
molecular beam epitaxial growth of wide gap II–VI injection lasers and light-emitting diodes, 190

Gallium
Si/SiGe heterostructures and devices, 125

Gallium arsenide
growth of high quality AlGaAs/GaAs heterostructures by molecular beam epitaxy for photonic and electronic device applications, 143
molecular beam epitaxial GaAs grown at low temperatures, 61
molecular beam epitaxy for high electron mobility modulation-doped two-dimensional gases, 74
pseudomorphic InGaAs high electron mobility transistors, 95
review of III–V semiconductor based metal–insulator–semiconductor structures and devices, 107
transport of quasi-two-dimensional electrons in heterojunction field effect transistors, 86

Gallium selenide
reflection high energy electron diffraction measurements of molecular beam epitaxially grown GaAs and InGaAs on GaAs(111), 1

Growth mechanism
reflection high energy electron diffraction measurements of molecular beam epitaxially grown GaAs and InGaAs on GaAs(111), 1
surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures, 43

Hall effect
molecular beam epitaxial GaAs grown at low temperatures, 61

Heterostructures
gas source molecular beam epitaxial growth and characterization of 600–660 nm GaInP/AlInP double-heterostructure lasers, 173
growth of semiconductor heterostructures on patterned substrates: defect reduction and nanostructures, 8
Si/SiGe heterostructures and devices, 125
transport of quasi-two-dimensional electrons in heterojunction field effect transistors, 86

High energy electron diffraction
reflection high energy electron diffraction measurements of molecular beam epitaxially grown GaAs and InGaAs on GaAs(111), 1

Indium
pseudomorphic InGaAs high electron mobility transistors, 95
review of III–V semiconductor based metal–insulator–semiconductor structures and devices, 107

Interfaces
review of III–V semiconductor based metal–insulator–semiconductor structures and devices, 107

Molecular beam epitaxy
gas source molecular beam epitaxial growth and characterization of 600–660 nm GaInP/AlInP double-heterostructure lasers, 173
growth of semiconductor heterostructures on patterned substrates: defect reduction and nanostructures, 8
molecular beam epitaxial GaAs grown at low temperatures, 61
molecular beam epitaxial growth of wide gap II–VI injection lasers and light-emitting diodes, 190
molecular beam epitaxy for high electron mobility modulation-doped two-dimensional electron gases, 74
progress and prospects for GaN and the III–V nitride semiconductors, 197
surfactant-mediated beam epitaxy of strained layer semidonductor heterostructures, 43
transport of quasi-two-dimensional electrons in heterojunction field effect transistors, 86

Nanostructures
growth of semiconductor heterostructures on patterned substrates: defect reduction and nanostructures, 8
molecular beam epitaxial growth of wide gap II–VI injection lasers and light-emitting diodes, 190
molecular beam epitaxy for high electron mobility modulation-doped two-dimensional electron gases, 74

Nitrides
progress and prospects for GaN and the III–V nitride semiconductors, 197

Optical properties
surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures, 43

Quantum effects
molecular beam epitaxy for high electron mobility modulation-doped two-dimensional electron gases, 74

Resistivity
molecular beam epitaxial GaAs grown at low temperatures, 61

Semiconductors
gas source molecular beam epitaxial growth and characterization of 600–660 nm GaInP/AlInP double-heterostructure lasers, 173
gas source molecular beam epitaxial growth and device applications in $In_{0.5}Ga_{0.5}P$ and $In_{0.5}Al_{0.5}P$ heterostructures, 158

molecular beam epitaxial growth of wide gap II–VI injection lasers and light-emitting diodes, 190
progress and prospects for GaN and the III–V nitride semiconductors, 197
review of III–V semiconductor based metal–insulator–semiconductor structures and devices, 107
Silicon
Si/SiGe heterostructures and devices, 125
Structural properties
surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures, 43
Superlattices
gas source molecular beam epitaxial growth and characterization on 600–660 nm GaInP/AlInP double-heterostructure lasers, 173
Surface defects
growth of semiconductor heterostructures on patterned substrates: defect reduction and nanostructures, 8
Surface diffusion
reflection high energy electron diffraction measurements of molecular beam epitaxially grown GaAs and InGaAs on GaAs(111), 1